VS-20ETS08FP-M3, VS-20ETS12FP-M3

Vishay Semiconductors

COMPLIANT

HALOGEN

FREE

High Voltage, Input Rectifier Diode, 20 A





TO-220 FullPAK 2L

PRIMARY CHARACTERISTICS				
I _{F(AV)}	20 A			
V_R	800 V, 1200 V			
V _F at I _F	1.1 V			
I _{FSM}	300 A			
T _J max.	150 °C			
Package	TO-220 FullPAK 2L			
Circuit configuration	Single			

FEATURES

- · Very low forward voltage drop
- 150 °C max. operating junction temperature
- · Glass passivated pellet chip junction
- Designed and qualified according to JEDEC®-JESD 47
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

APPLICATIONS

- · Input rectification
- Vishay Semiconductors switches and output rectifiers which are available in identical package outlines

DESCRIPTION

High voltage rectifiers optimized for very low forward voltage drop with moderate leakage.

These devices are intended for use in main rectification (single or three phase bridge).

OUTPUT CURRENT IN TYPICAL APPLICATIONS					
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS		
Capacitive input filter $T_A = 55$ °C, $T_J = 125$ °C common heatsink of 1 °C/W	18	22	А		

MAJOR RATINGS AND CHARACTERISTICS						
SYMBOL	CHARACTERISTICS	CHARACTERISTICS VALUES UNITS				
I _{F(AV)}	Sinusoidal waveform	20	Α			
V_{RRM}	Range	800, 1200	V			
I _{FSM}		300	Α			
V _F	10 A, T _J = 25 °C	1.0	V			
TJ		-40 to +150	°C			

VOLTAGE RATINGS						
PART NUMBER	V _{RRM} , MAXIMUM PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	I _{RRM} AT 150 °C mA			
VS-20ETS08FP-M3	800 900					
VS-20ETS12FP-M3	1200	1300	ı			



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ABSOLUTE MAXIMUM RATINGS	S			
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum average forward current	I _{F(AV)}	T _C = 51 °C, 180° conduction half sine wave	20	
Maximum peak one cycle		10 ms sine pulse, rated V _{RRM} applied	250	А
non-repetitive surge current	IFSM	10 ms sine pulse, no voltage reapplied	300	
Maximum I ² t for fusing	I ² t	10 ms sine pulse, rated V _{RRM} applied	316	A ² s
Maximum i-t for fusing	iximum i-t for fusing	10 ms sine pulse, no voltage reapplied	442	A-S
Maximum I ² √t for fusing	I²√t	t = 0.1 ms to 10 ms, no voltage reapplied	4420	A²√s

ELECTRICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST (CONDITIONS	VALUES	UNITS
Maximum forward voltage drop	V_{FM}	20 A, T _J = 25 °C		1.1	V
Forward slope resistance	r _t	r_t $V_{F(TO)}$ $T_J = 150 ^{\circ}C$		10.4	m $Ω$
Threshold voltage	V _{F(TO)}			0.85	V
Maximum reverse leakage current	1	T _J = 25 °C	V _B = Rated V _{BBM}	0.1	mA
iviaximum reverse leakage current	I _{RM}	T _J = 150 °C	v _R = nateu v _{RRM}	1.0	IIIA

THERMAL - MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage tempera	ature range	T _J , T _{Stg}		-40 to +150	°C
Maximum thermal resistance, junction to case		R _{thJC}	DC operation	2.8	
Maximum thermal resistance, junction to ambient		R _{thJA}		62	°C/W
Typical thermal resistance, case to heatsink		R _{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight				2	g
Approximate weight				0.07	OZ.
Mounting torque ———	minimum			6.0 (5.0)	kgf · cm
	maximum			12 (10)	(lbf \cdot in)
Mayling davisa			Occasional TO 200 F HDAK O	20ETS	S08FP
Marking device			Case style TO-220 FullPAK 2L	20ETS	S12FP

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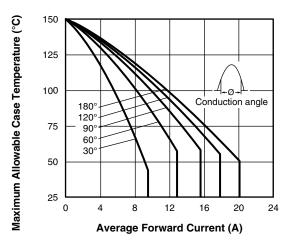


Fig. 1 - Current Rating Characteristics

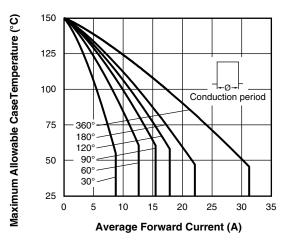


Fig. 2 - Current Rating Characteristics

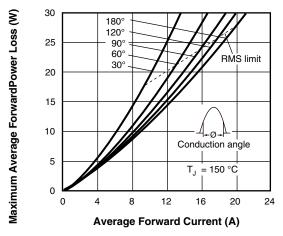


Fig. 3 - Forward Power Loss Characteristics

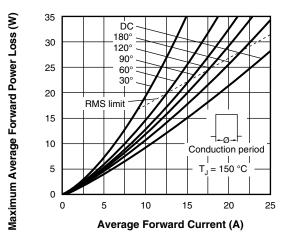


Fig. 4 - Forward Power Loss Characteristics

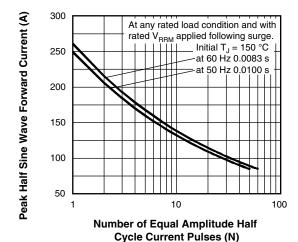


Fig. 5 - Maximum Non-Repetitive Surge Current

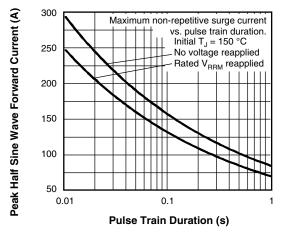


Fig. 6 - Maximum Non-Repetitive Surge Current

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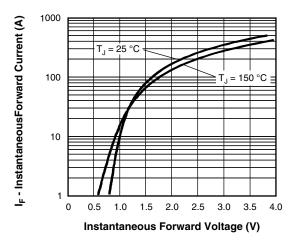


Fig. 7 - Forward Voltage Drop Characteristics

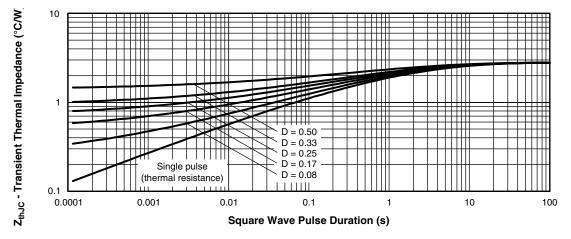


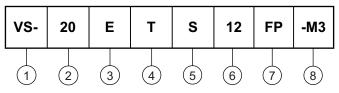
Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

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ORDERING INFORMATION TABLE





1 - Vishay Semiconductors product

- Current rating (20 = 20 A)

- Circuit configuration:

E = single diode

- Package:

4 T = TO-220

- Type of silicon:

S = standard recovery rectifier

08 = 800 V 12 = 1200 V

Voltage ratingsFullPAK

8 - Environmental digit:

-M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)					
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION		
VS-20ETS08FP-M3	50	1000	Antistatic plastic tubes		
VS-20ETS12FP-M3	50	1000	Antistatic plastic tubes		

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96157
Part marking information	www.vishay.com/doc?95392



Vishay Semiconductors

2L TO-220 FullPAK

DIMENSIONS in millimeters









Bottom view



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